Data Sheet | July 11, 2006 | FN6295.1

100V, 3A/4A Peak, High Frequency Half-Bridge Drivers

The ISL2110, ISL2111 are 100V, high frequency, half-bridge N-channel power MOSFET driver ICs. They are based on the popular HIP2100, HIP2101 half-bridge drivers, but offer several performance improvements. Peak output pull-up/pull-down current has been increased to 3A/4A, which significantly reduces switching power losses and eliminates the need for external totem-pole buffers in many applications. Also, the low end of the V_{DD} operational supply range has been extended to 8VDC. The ISL2110 has additional input hysteresis for superior operation in noisy environments and the inputs of the ISL2111, like those of the ISL2110, can now safely swing to the V_{DD} supply rail.

Ordering Information

PART NUMBER (Notes 1, 2)	PART MARKING	TEMP. RANGE (°C)	PACKAGE (Pb-Free)	PKG. DWG. #
ISL2110ABZ	2110ABZ	-40 to 125	8 Ld SOIC	M8.15
ISL2110AR4Z	2110AR4Z	-40 to 125	12 Ld 4x4 DFN	L12.4x4A
ISL2111ABZ	2111ABZ	-40 to 125	8 Ld SOIC	M8.15
ISL2111AR4Z	2111AR4Z	-40 to 125	12 Ld 4x4 DFN	L12.4x4A

NOTES:

1. Intersil Pb-free plus anneal products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
2. Add “-T” suffix for Tape and Reel packing option.

Features

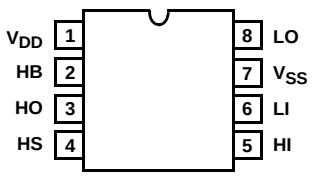
- Drives N-Channel MOSFET Half-Bridge
- SOIC and DFN Package Options
- SOIC and DFN Packages Compliant with 100V Conductor Spacing Guidelines per IPC-2221
- Pb-Free Plus Anneal Available (RoHS Compliant)
- Bootstrap Supply Max Voltage to 114VDC
- On-Chip 1Ω Bootstrap Diode
- Fast Propagation Times for Multi-MHz Circuits
- Drives 1nF Load with Typical Rise/Fall Times of 9ns/7.5ns
- CMOS Compatible Input Thresholds (ISL2110)
- 3.3V/TTL Compatible Input Thresholds (ISL2111)
- Independent Inputs Provide Flexibility
- No Start-Up Problems
- Outputs Unaffected by Supply Glitches, HS Ringing Below Ground or HS Slewing at High dv/dt
- Low Power Consumption
- Wide Supply Voltage Range (8V to 14V)
- Supply Undervoltage Protection
- 1.6Ω/1Ω Typical Output Pull-Up/Pull-Down Resistance

Applications

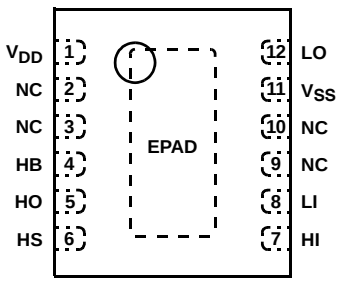
- Telecom Half-Bridge DC/DC Converters
- Telecom Full-Bridge DC/DC Converters
- Two-Switch Forward Converters
- Active-Clamp Forward Converters
- Class-D Audio Amplifiers

Pinouts

ISL2110, ISL2111 (SOIC)
TOP VIEW

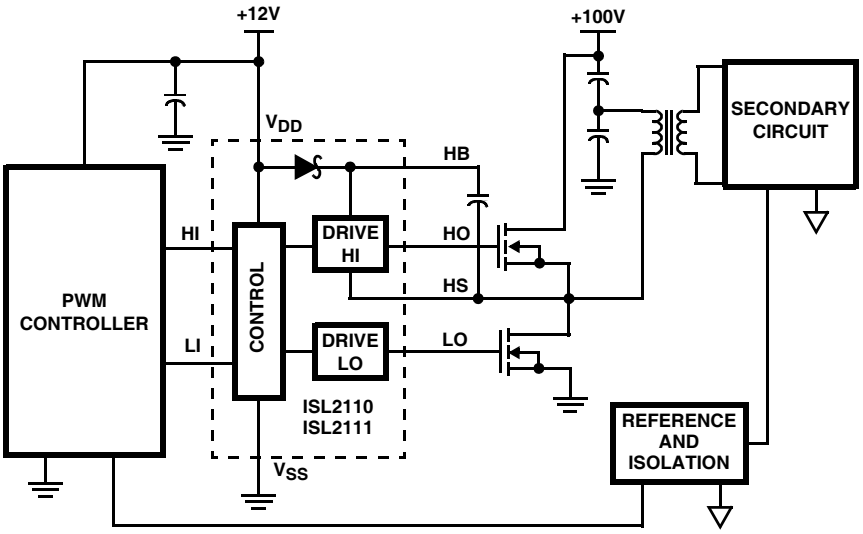


ISL2110, ISL2111 (DFN)
TOP VIEW

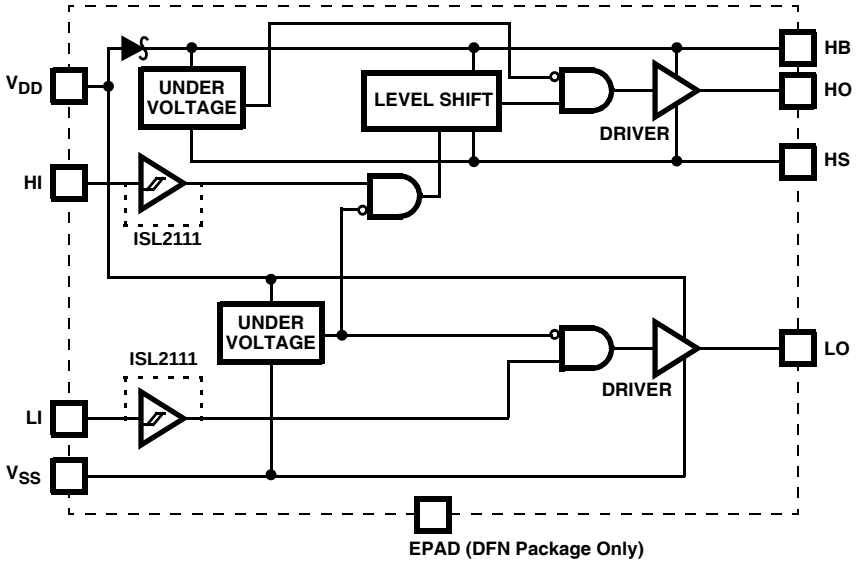


NOTE: EPAD = Exposed PAD.

Application Block Diagram



Functional Block Diagram



*EPAD = Exposed Pad. The EPAD is electrically isolated from all other pins. For best thermal performance connect the EPAD to the PCB power ground plane.

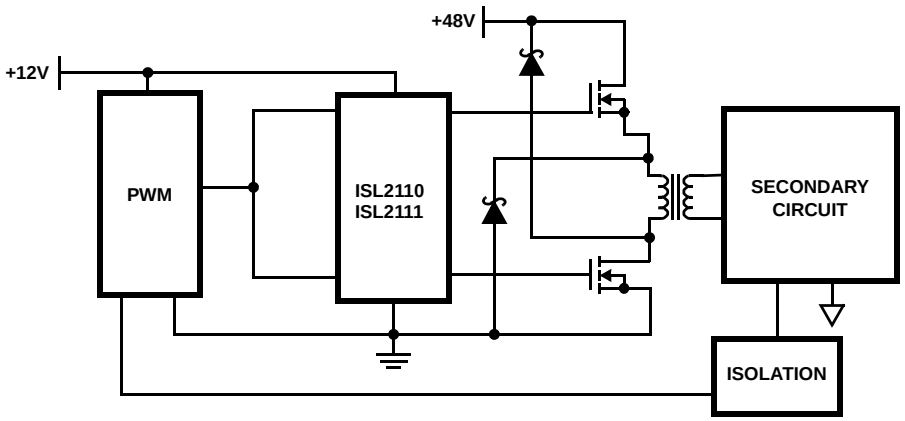


FIGURE 1. TWO-SWITCH FORWARD CONVERTER

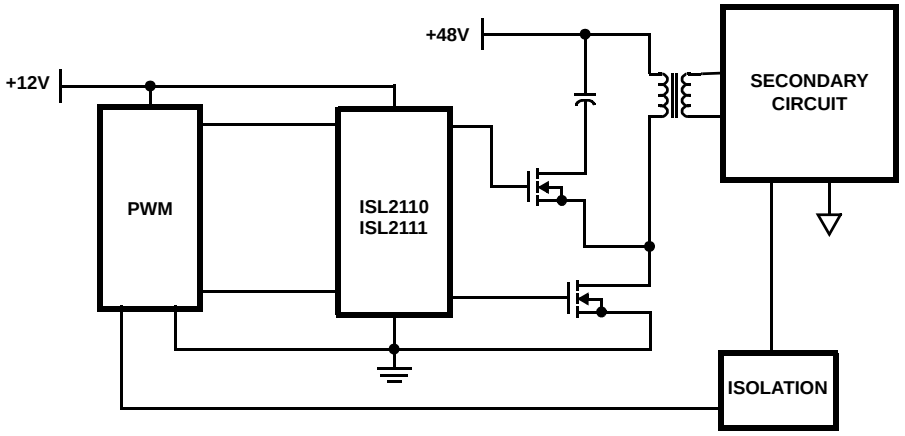


FIGURE 2. FORWARD CONVERTER WITH AN ACTIVE-CLAMP

Absolute Maximum Ratings

Supply Voltage, V_{DD}, V_{HB} - V_{HS} (Notes 3, 4) . . . . . -0.3V to 18V
LI and HI Voltages (Note 4) . . . . . -0.3V to V_{DD} + 0.3V
Voltage on LO (Note 4) . . . . . -0.3V to V_{DD} + 0.3V
Voltage on HO (Note 4) . . . . . V_{HS} - 0.3V to V_{HB} + 0.3V
Voltage on HS (Continuous) (Note 4) . . . . . -1V to 110V
Voltage on HB (Note 4) 118V
Average Current in V_{DD} to HB Diode 100mA

Maximum Recommended Operating Conditions

Supply Voltage, V_{DD} . . . . . 8V to 14V
Voltage on HS . . . . . -1V to 100V
Voltage on HS . . . . . (Repetitive Transient) -5V to 105V
Voltage on HB . . V_{HS} + 7V to V_{HS} + 14V and V_{DD} - 1V to V_{DD} + 100V
HS Slew Rate. . . . . <50V/ns

Thermal Information

Thermal Resistance (Typical)	θ_{JA} (°C/W)	θ_{JC} (°C/W)
SOIC (Note 5)	95	N/A
DFN (Note 6)	40	3

Max Power Dissipation at 25°C in Free Air (SOIC, Note 5) 1.3W
Max Power Dissipation at 25°C in Free Air (DFN, Note 6) 3.1W
Storage Temperature Range . . . . . -65°C to 150°C
Junction Temperature Range. . . . . -55°C to 150°C
Lead Temperature (Soldering 10s - SOIC Lead Tips Only) . . . 300°C
For recommended soldering conditions see Tech Brief TB389.

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the recommended operating conditions of this specification is not implied.

NOTES:

3. The ISL2110 and ISL2111 are capable of derated operation at supply voltages exceeding 14V. Figure 22 shows the high-side voltage derating curve for this mode of operation.
4. All voltages referenced to V_{SS} unless otherwise specified.
5. θ_{JA} is measured in free air with the component mounted on a high effective thermal conductivity test board. See Tech Brief TB379 for details.
6. θ_{JA} is measured in free air with the component mounted on a high effective thermal conductivity test board with "direct attach" features. For θ_{JC}, the "case temp" is measured at the center of the exposed metal pad on the package underside. See Tech Brief TB379 for details.

Electrical Specifications

V_{DD} = V_{HB} = 12V, V_{SS} = V_{HS} = 0V, No Load on LO or HO, Unless Otherwise Specified

PARAMETERS	SYMBOL	TEST CONDITIONS	T_J = 25°C			T_J = -40°C to 125°C		UNITS
			MIN	TYP	MAX	MIN	MAX	
SUPPLY CURRENTS								
V_{DD} Quiescent Current	I_{DD}	ISL2110; LI = HI = 0V	-	0.1	0.25	-	0.3	mA
V_{DD} Quiescent Current	I_{DD}	ISL2111; LI = HI = 0V	-	0.3	0.45	-	0.55	mA
V_{DD} Operating Current	I_{DDO}	ISL2110; f = 500kHz	-	3.4	5.0	-	5.5	mA
V_{DD} Operating Current	I_{DDO}	ISL2111; f = 500kHz	-	3.5	5.0	-	5.5	mA
Total HB Quiescent Current	I_{HB}	LI = HI = 0V	-	0.1	0.15	-	0.2	mA
Total HB Operating Current	I_{HBO}	f = 500kHz	-	3.4	5.0	-	5.5	mA
HB to V_{SS} Current, Quiescent	I_{HBS}	LI = HI = 0V; V_{HB} = V_{HS} = 114V	-	0.05	1.5	-	10	µA
HB to V_{SS} Current, Operating	I_{HBSO}	f = 500kHz; V_{HB} = V_{HS} = 114V	-	1.2	-	-	-	mA
INPUT PINS								
Low Level Input Voltage Threshold	V_{IL}	ISL2110	3.7	4.4	-	3.5	-	V
Low Level Input Voltage Threshold	V_{IL}	ISL2111	1.4	1.8	-	1.2	-	V
High Level Input Voltage Threshold	V_{IH}	ISL2110	-	6.6	7.4	-	7.6	V
High Level Input Voltage Threshold	V_{IH}	ISL2111	-	1.8	2.2	-	2.4	V
Input Voltage Hysteresis	V_{IHYS}	ISL2110	-	2.2	-	-	-	V
Input Pull-down Resistance	R_I		-	210	-	100	500	kΩ
UNDER VOLTAGE PROTECTION								
V_{DD} Rising Threshold	V_{DDR}		6.1	6.6	7.1	5.8	7.4	V
V_{DD} Threshold Hysteresis	V_{DDH}		-	0.6	-	-	-	V

Electrical Specifications $V_{DD} = V_{HB} = 12V$, $V_{SS} = V_{HS} = 0V$, No Load on LO or HO, Unless Otherwise Specified **(Continued)**

PARAMETERS	SYMBOL	TEST CONDITIONS	T_J = 25°C			T_J = -40°C to 125°C		UNITS
			MIN	TYP	MAX	MIN	MAX	
HB Rising Threshold	V_{HBR}		5.5	6.1	6.8	5.0	7.1	V
HB Threshold Hysteresis	V_{HBH}		-	0.6	-	-	-	V
BOOT STRAP DIODE								
Low Current Forward Voltage	V_{DL}	I_{VDD-HB} = 100µA	-	0.5	0.6	-	0.7	V
High Current Forward Voltage	V_{DH}	I_{VDD-HB} = 100mA	-	0.7	0.9	-	1	V
Dynamic Resistance	R_D	I_{VDD-HB} = 100mA	-	0.7	1	-	1.5	Ω
LO GATE DRIVER								
Low Level Output Voltage	V_{OLL}	I_{LO} = 100mA	-	0.1	0.18	-	0.25	V
High Level Output Voltage	V_{OHL}	I_{LO} = -100mA, $V_{OHL} = V_{DD} - V_{LO}$	-	0.16	0.23	-	0.3	V
Peak Pull-Up Current	I_{OHL}	V_{LO} = 0V	-	3	-	-	-	A
Peak Pull-Down Current	I_{OLL}	V_{LO} = 12V	-	4	-	-	-	A
HO GATE DRIVER								
Low Level Output Voltage	V_{OLH}	I_{HO} = 100mA	-	0.1	0.18	-	0.25	V
High Level Output Voltage	V_{OHH}	I_{HO} = -100mA, $V_{OHH} = V_{HB} - V_{HO}$	-	0.16	0.23	-	0.3	V
Peak Pull-Up Current	I_{OHH}	V_{HO} = 0V	-	3	-	-	-	A
Peak Pull-Down Current	I_{OLH}	V_{HO} = 12V	-	4	-	-	-	A

Switching Specifications $V_{DD} = V_{HB} = 12V$, $V_{SS} = V_{HS} = 0V$, No Load on LO or HO, Unless Otherwise Specified

PARAMETERS	SYMBOL	TEST CONDITIONS	T_J = 25°C			T_J = -40°C to 125°C		UNITS
			MIN	TYP	MAX	MIN	MAX	
Lower Turn-Off Propagation Delay (LI Falling to LO Falling)	t_{LPHL}		-	32	50	-	60	ns
Upper Turn-Off Propagation Delay (HI Falling to HO Falling)	t_{HPHL}		-	32	50	-	60	ns
Lower Turn-On Propagation Delay (LI Rising to LO Rising)	t_{LPLH}		-	39	50	-	60	ns
Upper Turn-On Propagation Delay (HI Rising to HO Rising)	t_{HPLH}		-	38	50	-	60	ns
Delay Matching: Upper Turn-Off to Lower Turn-On	t_{MON}		1	8	-	-	16	ns
Delay Matching: Lower Turn-Off to Upper Turn-On	t_{MOFF}		1	6	-	-	16	ns
Either Output Rise Time (10% to 90%)	t_{RC}	C_L = 1nF	-	9	-	-	-	ns
Either Output Fall Time (90% to 10%)	t_{FC}	C_L = 1nF	-	7.5	-	-	-	ns
Either Output Rise Time (3V to 9V)	t_R	C_L = 0.1µF	-	0.3	0.4	-	0.5	µs
Either Output Fall Time (9V to 3V)	t_F	C_L = 0.1µF	-	0.19	0.3	-	0.4	µs
Minimum Input Pulse Width that Changes the Output	t_{PW}		-	-	-	-	50	ns
Bootstrap Diode Turn-On or Turn-Off Time	t_{BS}		-	10	-	-	-	ns

Pin Descriptions

SYMBOL	DESCRIPTION
V_{DD}	Positive supply to lower gate driver. Bypass this pin to V_{SS}.
HB	High-side bootstrap supply. External bootstrap capacitor is required. Connect positive side of bootstrap capacitor to this pin. Bootstrap diode is on-chip.
HO	High-side output. Connect to gate of high-side power MOSFET.
HS	High-side source connection. Connect to source of high-side power MOSFET. Connect negative side of bootstrap capacitor to this pin.
HI	High-side input.
LI	Low-side input.
V_{SS}	Chip negative supply, which will generally be ground.
LO	Low-side output. Connect to gate of low-side power MOSFET.
EPAD	Exposed pad. Connect to ground or float. The EPAD is electrically isolated from all other pins.

Timing Diagrams

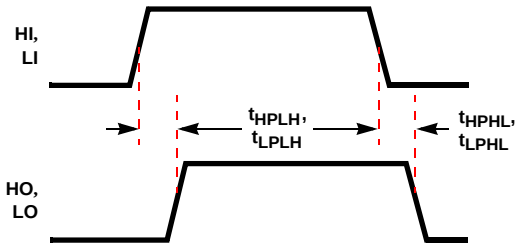


FIGURE 3. PROPAGATION DELAYS

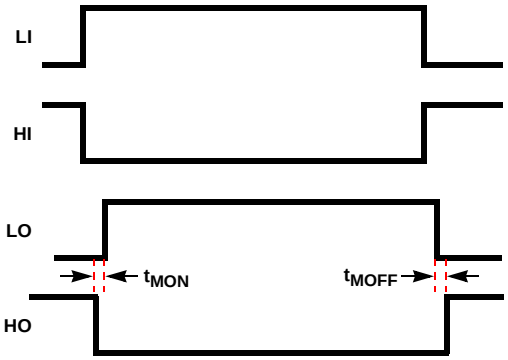


FIGURE 4. DELAY MATCHING

Typical Performance Curves

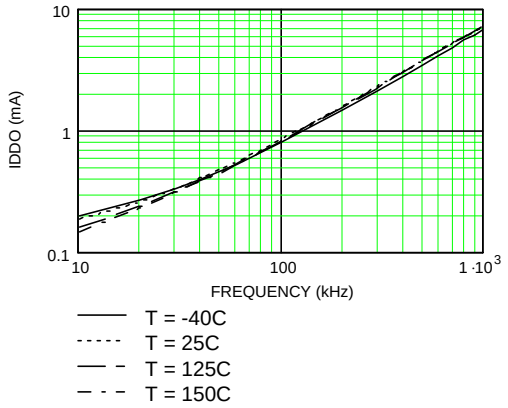


FIGURE 5. ISL2110 IDD OPERATING CURRENT vs FREQUENCY

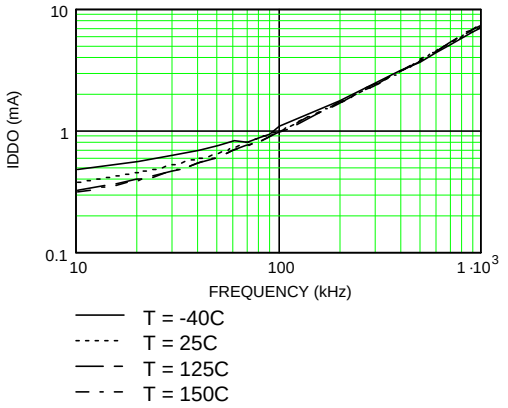


FIGURE 6. ISL2111 IDD OPERATING CURRENT vs FREQUENCY

Typical Performance Curves (Continued)

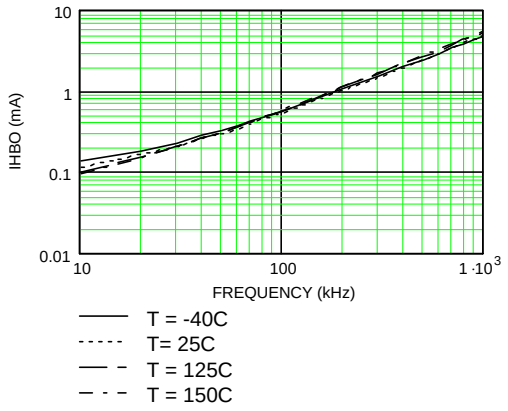


FIGURE 7. IHB OPERATING CURRENT vs FREQUENCY

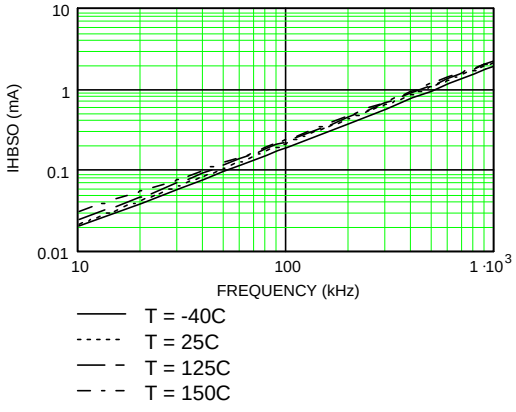


FIGURE 8. IHBS OPERATING CURRENT vs FREQUENCY

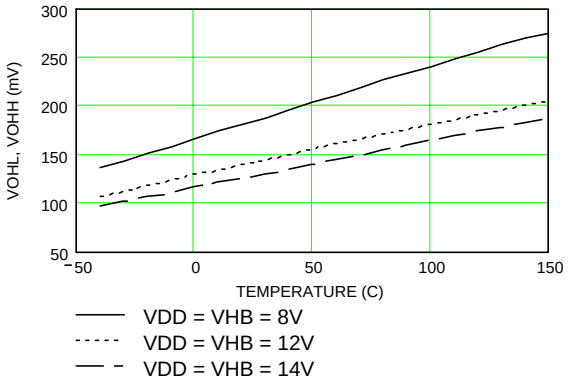


FIGURE 9. HIGH LEVEL OUTPUT VOLTAGE vs TEMPERATURE

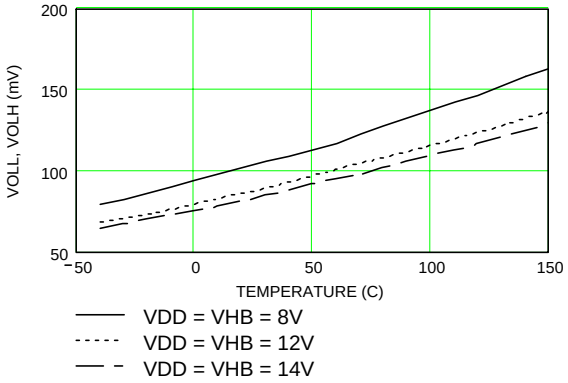


FIGURE 10. LOW LEVEL OUTPUT VOLTAGE vs TEMPERATURE

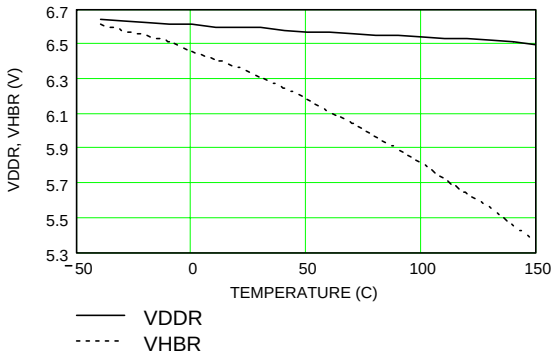


FIGURE 11. UNDERVOLTAGE LOCKOUT THRESHOLD vs TEMPERATURE

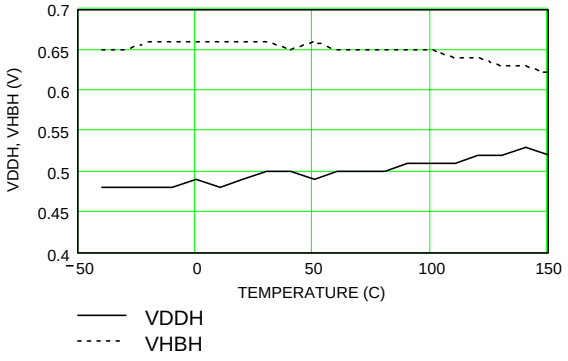


FIGURE 12. UNDERVOLTAGE LOCKOUT HYSTERESIS vs TEMPERATURE

Typical Performance Curves (Continued)

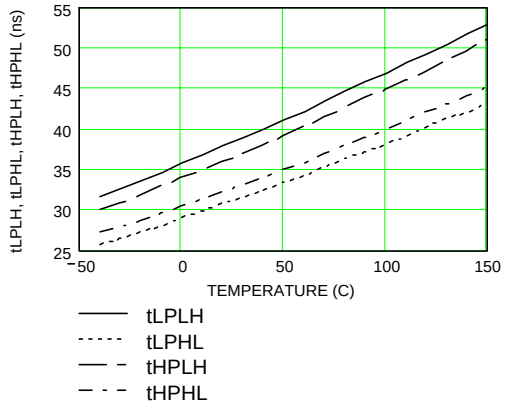


FIGURE 13. ISL2110 PROPAGATION DELAYS vs TEMPERATURE

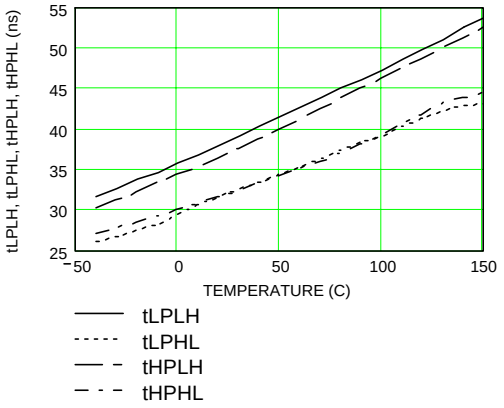


FIGURE 14. ISL2111 PROPAGATION DELAYS vs TEMPERATURE

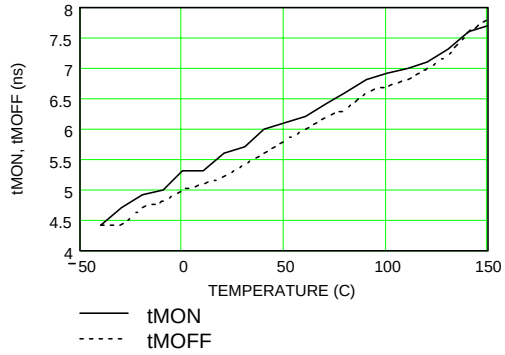


FIGURE 15. ISL2110 DELAY MATCHING vs TEMPERATURE

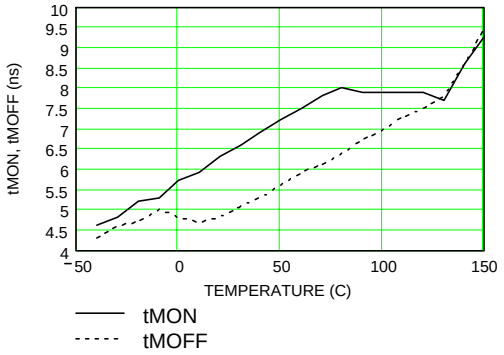


FIGURE 16. ISL2111 DELAY MATCHING vs TEMPERATURE

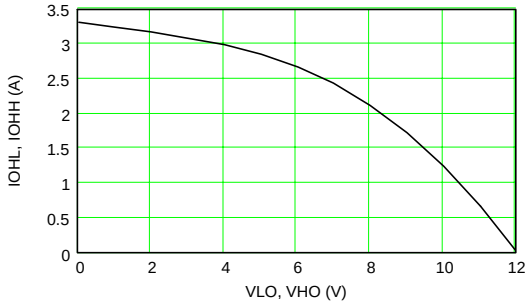


FIGURE 17. PEAK PULL-UP CURRENT vs OUTPUT VOLTAGE

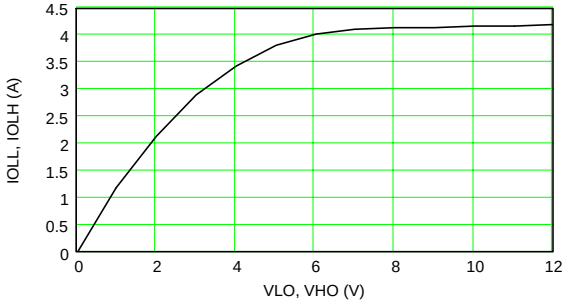


FIGURE 18. PEAK PULL-DOWN CURRENT vs OUTPUT VOLTAGE

Typical Performance Curves (Continued)

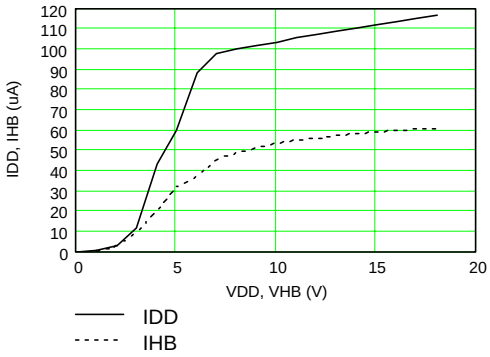


FIGURE 19. ISL2110 QUIESCENT CURRENT vs VOLTAGE

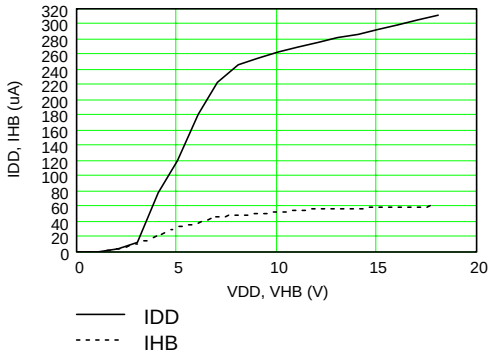


FIGURE 20. ISL2111 QUIESCENT CURRENT vs VOLTAGE

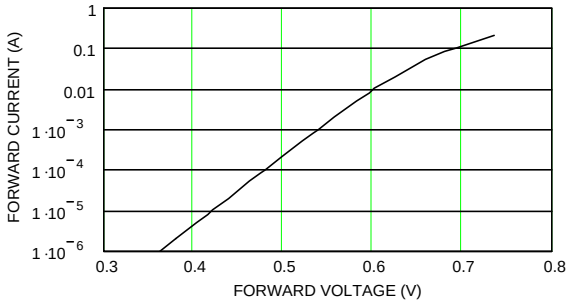


FIGURE 21. BOOTSTRAP DIODE I-V CHARACTERISTICS

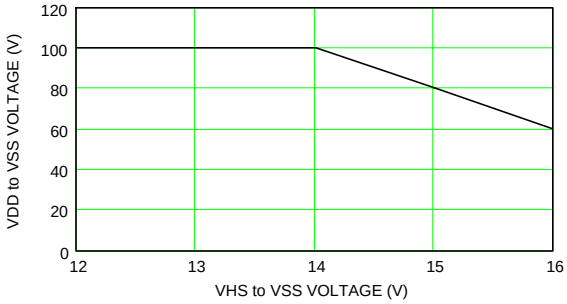
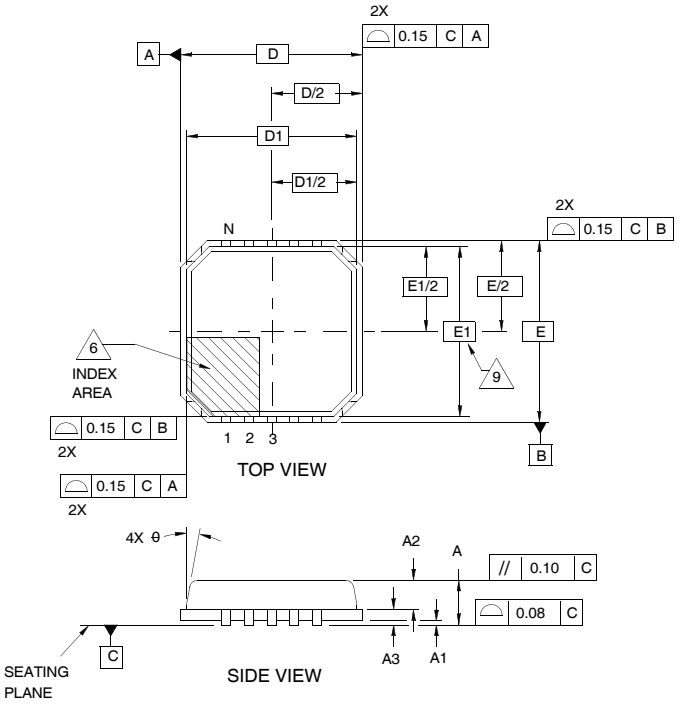
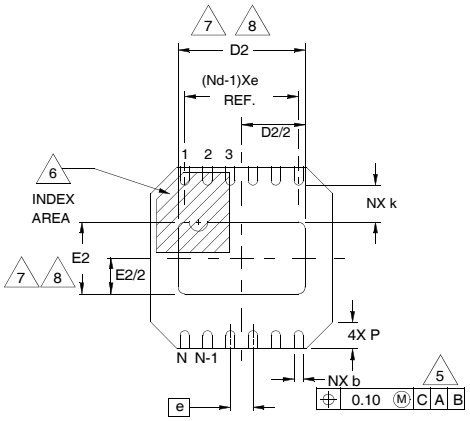
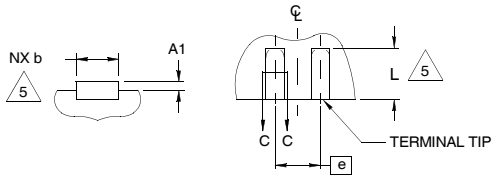


FIGURE 22. VHS VOLTAGE vs VDD VOLTAGE

Dual Flat No-Lead Plastic Package (DFN)
Micro Lead Frame Plastic Package (MLFP)







L12.4x4A

12 LEAD DUAL FLAT NO-LEAD PLASTIC PACKAGE

SYMBOL	MILLIMETERS			NOTES
	MIN	NOMINAL	MAX	
A	-	0.85	0.90	-
A1	0.00	0.01	0.05	-
A2	-	0.65	0.70	-
A3		0.20 REF		-
b	0.18	0.23	0.30	5, 8
D		4.00 BSC		-
D1		3.75 BSC		-
D2	2.65	2.80	2.95	7, 8
E		4.00 BSC		-
E1		3.75 BSC		-
E2	1.43	1.58	1.73	7, 8
e		0.50 BSC		-
k	0.635	-	-	-
L	0.30	0.40	0.50	8
N		12		2
Nd		6		3
P	0.24	0.42	0.60	-
θ	-	-	12	-

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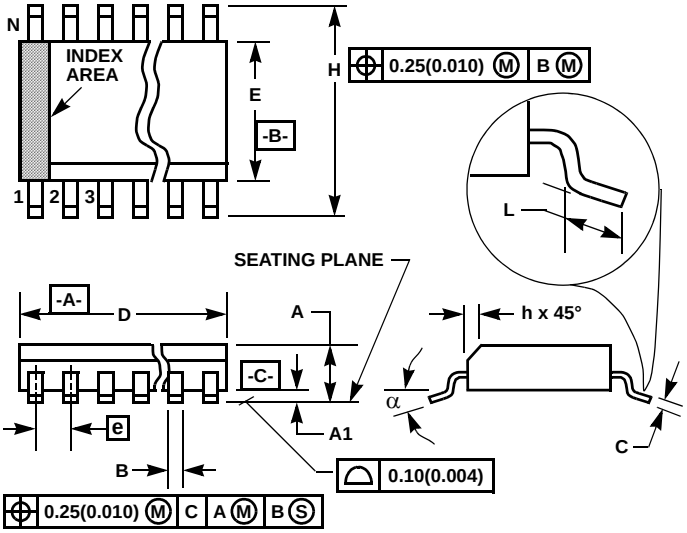
NOTES:

1. Dimensioning and tolerancing conform to ASME Y14.5M-1994.
2. N is the number of terminals.
3. Nd refer to the number of terminals on D.
4. All dimensions are in millimeters. Angles are in degrees.
5. Dimension b applies to the metallized terminal and is measured between 0.15mm and 0.30mm from the terminal tip.
6. The configuration of the pin #1 identifier is optional, but must be located within the zone indicated. The pin #1 identifier may be either a mold or mark feature.
7. Dimensions D2 and E2 are for the exposed pads which provide improved electrical and thermal performance.
8. Nominal dimensions are provided to assist with PCB Land Pattern Design efforts, see Intersil Technical Brief TB389.
9. COMPLIANT TO JEDEC MO-229-VGGD-2 ISSUE C except for the L dimension**.**

Small Outline Plastic Packages (SOIC)



NOTES:

1. Symbols are defined in the “MO Series Symbol List” in Section 2.2 of Publication Number 95.
2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
3. Dimension “D” does not include mold flash, protrusions or gate burrs. Mold flash, protrusion and gate burrs shall not exceed 0.15mm (0.006 inch) per side.
4. Dimension “E” does not include interlead flash or protrusions. Interlead flash and protrusions shall not exceed 0.25mm (0.010 inch) per side.
5. The chamfer on the body is optional. If it is not present, a visual index feature must be located within the crosshatched area.
6. “L” is the length of terminal for soldering to a substrate.
7. “N” is the number of terminal positions.
8. Terminal numbers are shown for reference only.
9. The lead width “B”, as measured 0.36mm (0.014 inch) or greater above the seating plane, shall not exceed a maximum value of 0.61mm (0.024 inch).
10. Controlling dimension: MILLIMETER. Converted inch dimensions are not necessarily exact.

M8.15 (JEDEC MS-012-AA ISSUE C)
8 LEAD NARROW BODY SMALL OUTLINE PLASTIC PACKAGE

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.0532	0.0688	1.35	1.75	-
A1	0.0040	0.0098	0.10	0.25	-
B	0.013	0.020	0.33	0.51	9
C	0.0075	0.0098	0.19	0.25	-
D	0.1890	0.1968	4.80	5.00	3
E	0.1497	0.1574	3.80	4.00	4
e	0.050 BSC		1.27 BSC		-
H	0.2284	0.2440	5.80	6.20	-
h	0.0099	0.0196	0.25	0.50	5
L	0.016	0.050	0.40	1.27	6
N	8		8		7
α	0°	8°	0°	8°	-

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